

S/N 10/081,818

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Jerome M. Eldridge et al.

Examiner: Phuc Dang

Serial No.: 10/081,818

Group Art Unit: 2818

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ATOMIC LAYER DEPOSITION OF METAL OXIDE AND/OR LOW  
ASYMMETRICAL TUNNEL BARRIER INTERPOLY INSULATORS

AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111

Commissioner for Patents  
Washington, D.C. 20231

This paper is in response to the Office Action mailed on January 2, 2003. Please amend  
the above-identified patent application as follows.

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**IN THE TITLE**

Please amend the title throughout the USPTO records to read "ATOMIC LAYER DEPOSITION OF METAL OXIDE AND/OR LOW ASYMMETRICAL TUNNEL BARRIER INTERPOLY INSULATORS".

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